METHOD OF PROCESSING SUBSTRATE, METHOD OF MANUFACTURING SEMICONDUCTOR DEVICE, SUBSTRATE PROCESSING APPARATUS, AND PROGRAM

ABSTRACT

There is provided a technique that includes performing a first cycle of forming a layer containing a first element and a second element, the first cycle including performing: (a) supplying a first precursor gas containing the first element to a substrate including a recess on a surface of the substrate; (b) supplying a first adsorption inhibitor gas to the substrate; (c) supplying a second precursor gas containing the second element, different from the first element, to the substrate; and (d) supplying a reactant gas to the substrate, wherein a functional group formed on the substrate in (a) and (b) inhibits adsorption of the second precursor gas on the substrate, and wherein in at least a part of (c), the second precursor gas is supplied to the substrate on which the first precursor gas and the first adsorption inhibitor gas are adsorbed.

Fig. 4